Single FET Bus Switch

HITACHI

ADE-205-661 (Z)

Rev. 0 Jan. 2002

Description

The HD74CBT1G126 features a single high-speed line switch. The switch is disabled when the output enable (OE) input is low.

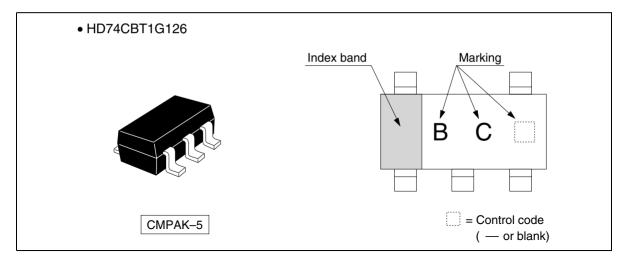
Features

- Minimal propagation delay through the switch.
- 5Ω switch connection between two ports.
- TTL-compatible input levels.
- Ultra low quiescent power. -Ideally suited for notebook applications.
- Package Type

Package type	Package code	Package suffix	Taping code		
CMPAK-5 pin	CMPAK-5	CM	E (3,000 pcs / Reel)		



Outline and Article Indication

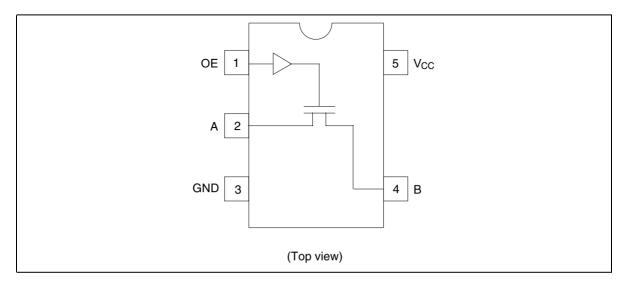


Function Table

Inpu	t OE	Function	
Н		A port = B port	
L		Disconnect	
H:	High level		
1.	Law laval		

L: Low level

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage range	V _{cc}	-0.5 to 7.0	V	
Input voltage range ¹	V ₁	-0.5 to 7.0	V	
Input clamp current	I _{IK}	-50	mA	V ₁ < 0
Continuous output current	I _o	128	mA	$V_{o} = 0$ to V_{cc}
Continuous current through V_{cc} or GND	$I_{\rm cc}$ or $I_{\rm gnd}$	±100	mA	
Maximum power dissipation at Ta = 25°C (in still air) 2	P _T	200	mW	
Storage temperature	Tstg	-65 to 150	°C	

Notes: The absolute maximum ratings are values which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

1. The input and output voltage ratings may be exceeded even if the input and output clamp-current ratings are observed.

2. The maximum package power dissipation was calculated using a junction temperature of 150°C.

Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage range	V _{cc}	4.0	5.5	V	
Input voltage range	V	0	5.5	V	
Output voltage range	V _{I/O}	0	5.5	V	
Input transition rise or fall rate	$\Delta t / \Delta v$	0	5	ns / V	V_{cc} = 4.5 to 5.5 V
Operating free-air temperature	Та	-40	85	°C	

Note: Unused or floating inputs must be held high or low.

DC Electrical Characteristics

 $(Ta = -40 \text{ to } 85^{\circ}\text{C})$

Item	Symbol	V_{cc} (V)	Min	Typ ^{*1}	Max	Unit	Test conditions
Clamp diode voltage	V _{IK}	4.5		_	-1.2	V	I _{IN} = -18 mA
Input voltage	V _{IH}	4.0 to 5.5	2.0	_		V	
	V _{IL}	4.0 to 5.5		_	0.8		
On-state switch resistance ²	R _{on}	4.0	_	14	20	Ω	$V_{IN} = 2.4 \text{ V},$ $I_{IN} = 15 \text{ mA}$ Typ at $V_{cc} = 4.0 \text{ V}$
		4.5	—	5	7	_	$V_{IN} = 0 V,$ $I_{IN} = 64 \text{ mA}$
		4.5	_	5	7		$V_{_{\rm IN}} = 0 V,$ $I_{_{\rm IN}} = 30 \text{ mA}$
		4.5	_	10	15		V _{IN} = 2.4 V, I _{IN} = 15 mA
Input current	I _{IN}	0 to 5.5		_	±1.0	μA	$V_{IN} = 5.5 \text{ V or GND}$
Off-state leakage current	I _{oz}	5.5	_	—	±1.0	μA	$0 \le A, B \le V_{cc}$
Quiescent supply current	I _{cc}	5.5	_		1.0	μA	$V_{IN} = V_{CC}$ or GND, $I_{O} = 0 \text{ mA}$
Increase in I_{cc} per input ^{'3}	ΔI_{cc}	5.5		_	2.5	mA	One input at 3.4 V, other inputs at V_{cc} or GND

Notes: For condition shown as Min or Max use the appropriate values under recommended operating conditions.

1. All typical values are at V_{cc} = 5 V (unless otherwise noted), Ta = 25°C.

2. Measured by the voltage drop between the A and B terminals at the indicated current through the switch. On-state resistance is determined by the lower voltage of the two (A or B) terminals.

3. This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{cc} or GND.

Capacitance

 $(Ta = 25^{\circ}C)$

Item	Symbol	V_{cc} (V)	Min	Тур	Max	Unit	Test conditions
Control input capacitance	C _{IN}	5.0	_	3	_	pF	$V_{IN} = 0 \text{ or } 3 \text{ V}$
Input / output capacitance	$\boldsymbol{C}_{\text{I/O (OFF)}}$	5.0	—	5	—	pF	$V_{o} = 0 \text{ or } 3 \text{ V}$ OE = GND

Note: This parameter is determined by device characterization is not production tested.

Switching Characteristics

 $(Ta = -40 \text{ to } 85^{\circ}\text{C})$

• $V_{cc} = 4.0 V$

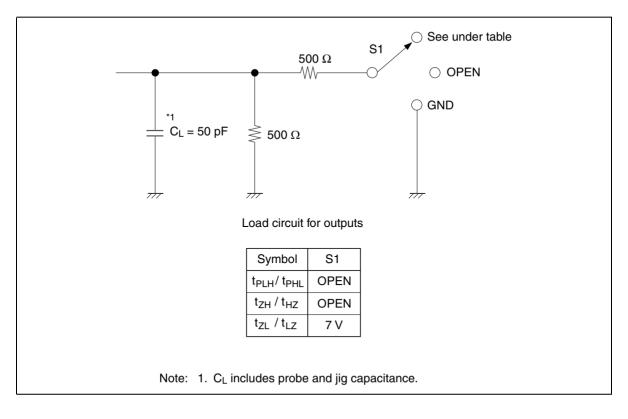
Item	Symbol	Min	Мах	Unit	Test conditions	FROM (Input)	TO (Output)
Propagation delay time ^{*1}	t _{PLH} t _{PHL}	_	0.35	ns	$C_{L} = 50 \text{ pF}$ $R_{L} = 500 \Omega$	A or B	B or A
Enable time	t _{zн} t _{z∟}	_	5.5	ns	$C_L = 50 \text{ pF}$ $R_L = 500 \Omega$	OE	A or B
Disable time	t _{HZ}		4.5	ns	$C_{L} = 50 \text{ pF}$	OE	A or B
	t _{LZ}	—	4.5	_	$R_{L} = 500 \Omega$		

• $V_{cc} = 5.0 \pm 0.5 \text{ V}$

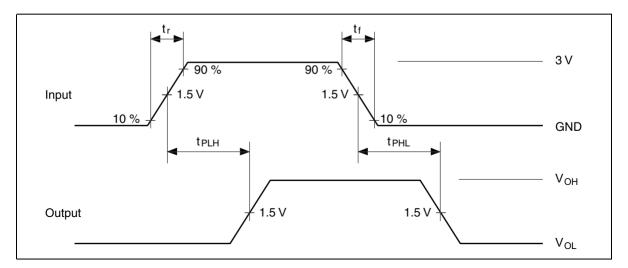
Item	Symbol	Min	Max	Unit	Test conditions	FROM (Input)	TO (Output)
Propagation delay time ^{*1}	t _{PLH} t _{PHL}	—	0.25	ns	$C_{L} = 50 \text{ pF}$ $R_{L} = 500 \Omega$	A or B	B or A
Enable time	t _{zH} t _{zL}	1.6	4.9	ns	$C_{L} = 50 \text{ pF}$ $R_{L} = 500 \Omega$	OE	A or B
Disable time	t _{HZ}	1.0	4.2	ns	C _L = 50 pF	OE	A or B
	t _{LZ}	1.0	4.8		$R_{L} = 500 \Omega$		

Note: 1. The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

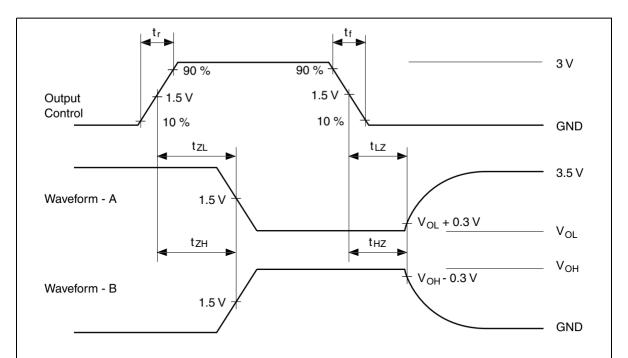
Test Circuit



Waveforms - 1

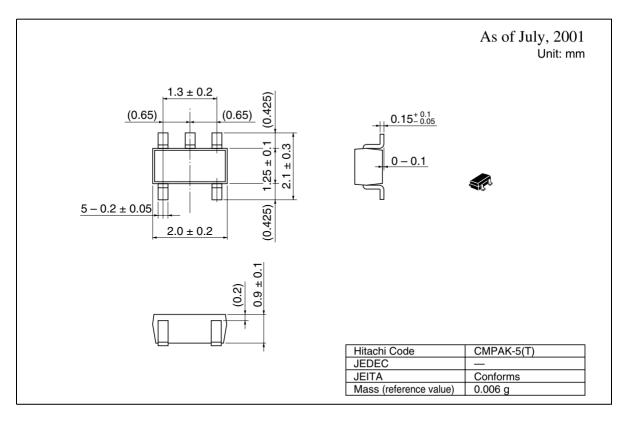


Waveforms – 2



- Notes: 1. All input pulses are supplied by generators having the following characteristics : $PRR \le 10 \text{ MHz}, Z_0 = 50 \Omega, t_f \le 2.5 \text{ ns}, t_f \le 2.5 \text{ ns}.$
 - 2. Waveform A is for an output with internal conditions such that the output is low except when disabled by the output control.
 - 3. Waveform B is for an output with internal conditions such that the output is high except when disabled by the output control.
 - 4. The output are measured one at a time with one transition per measurement.

Package Dimensions



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